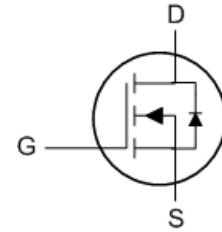




- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent Cdv/dt effect decline
- ★ Advanced high cell density Trench technology

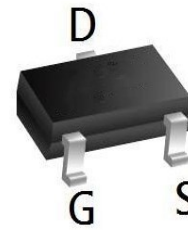


Description

The WL1002C is the high cell density trenched N-ch MOSFETs, which provides excellent RDSON and efficiency for most of the small power switching and load switch applications.

The WL1002C meet the RoHS and Green Product requirement with full function reliability approved.

SOT23 Pin Configuration



Product Summary

BVDSS	RDSON	ID
100V	220mΩ	2.2 A

Absolute Maximum Ratings (TA=25°C unless otherwise specified)

Symbol	Parameter	Max.	Units	
V _{DSS}	Drain-Source Voltage	100	V	
V _{GSS}	Gate-Source Voltage	±20	V	
I _D	Continuous Drain Current	T _A = 25°C	2.2	A
		T _A = 100°C	1.4	A
I _{DM}	Pulsed Drain Current ^{note1}	8.8	A	
P _D	Power Dissipation	T _A = 25°C	2.3	W
R _{θJA}	Thermal Resistance, Junction to Ambient	54	°C/W	
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +150	°C	

**Electrical Characteristics** ($T_J=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	100	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=100V, V_{GS}=0V$	-	-	1.0	μA
I_{GSS}	Gate to Body Leakage Current	$V_{DS}=0V, V_{GS}=\pm 20V$	-	-	± 100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0	1.5	2.2	V
$R_{DS(on)}$	Static Drain-Source on-Resistance <small>note2</small>	$V_{GS}=10V, I_D=2A$	-	220	286	m Ω
		$V_{GS}=4.5V, I_D=1A$	-	223	312	
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS}=25V, V_{GS}=0V,$ $f=1.0MHz$	-	321	-	pF
C_{oss}	Output Capacitance		-	21	-	pF
C_{riss}	Reverse Transfer Capacitance		-	15	-	pF
Q_g	Total Gate Charge	$V_{DS}=30V, I_D=2A,$ $V_{GS}=10V$	-	5.3	-	nC
Q_{gs}	Gate-Source Charge		-	1.3	-	nC
Q_{gd}	Gate-Drain("Miller") Charge		-	1.7	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	$V_{DS}=30V,$ $I_D=1A, R_{GEN}=3\Omega,$ $V_{GS}=10V$	-	14	-	ns
t_r	Turn-on Rise Time		-	54	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	18	-	ns
t_f	Turn-off Fall Time		-	11	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	2.2	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	8.8	A
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS}=0V, I_S=2.2A$	-	-	1.2	V

Notes: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 0.5\%$



Typical Performance Characteristics

Figure 1: Output Characteristics

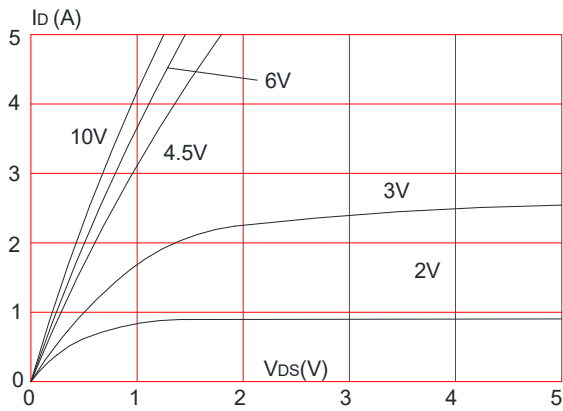


Figure 2: Typical Transfer Characteristics

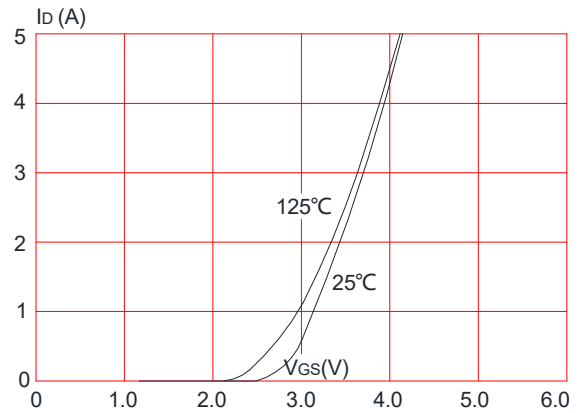


Figure 3: On-resistance vs. Drain Current

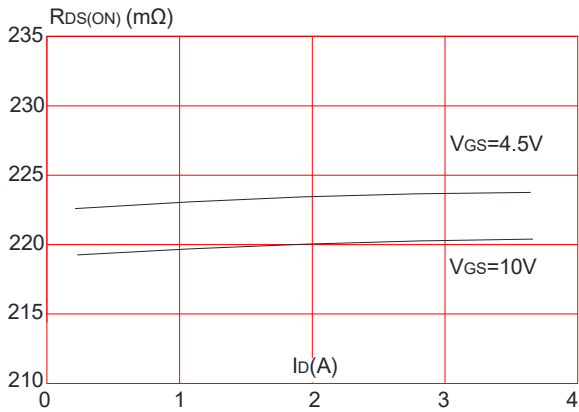


Figure 4: Body Diode Characteristics

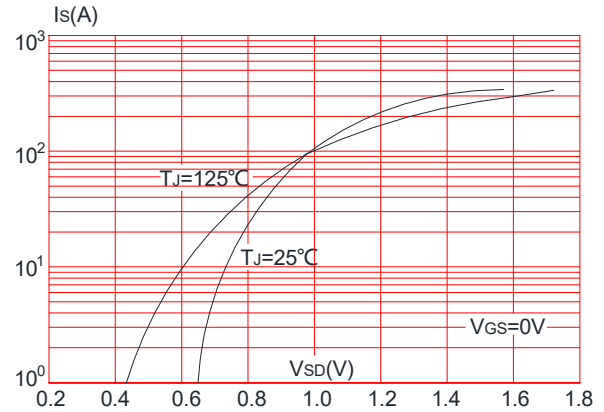


Figure 5: Gate Charge Characteristics

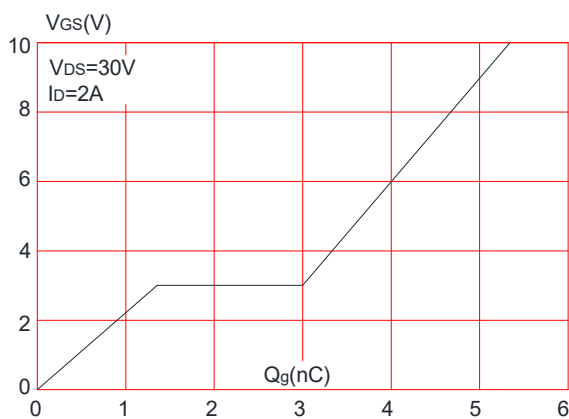


Figure 6: Capacitance Characteristics

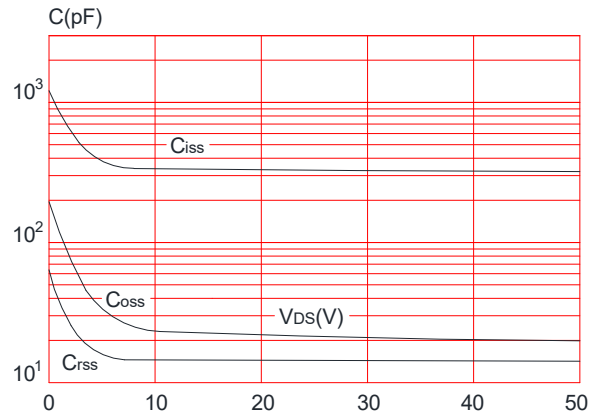




Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

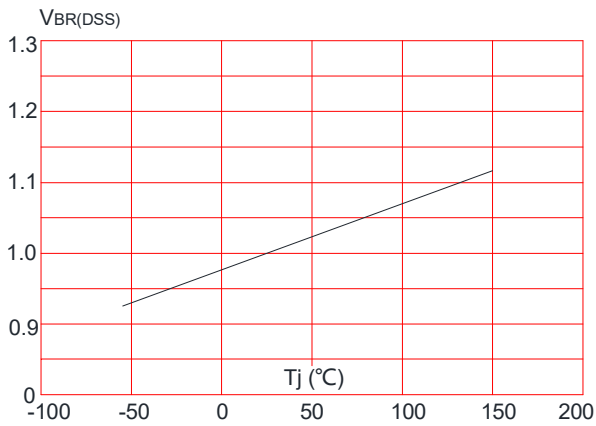


Figure 8: Normalized on Resistance vs. Junction Temperature

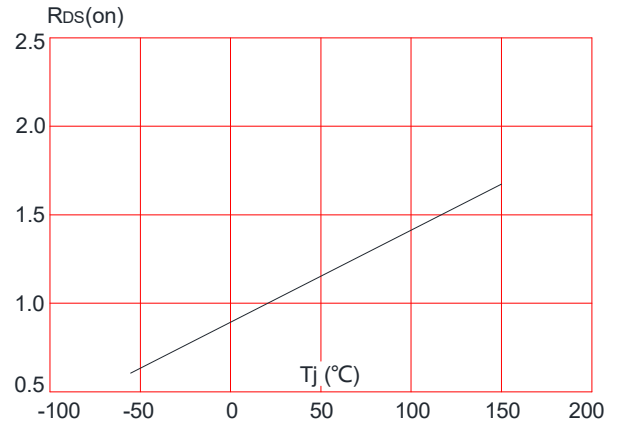


Figure 9: Maximum Safe Operating Area

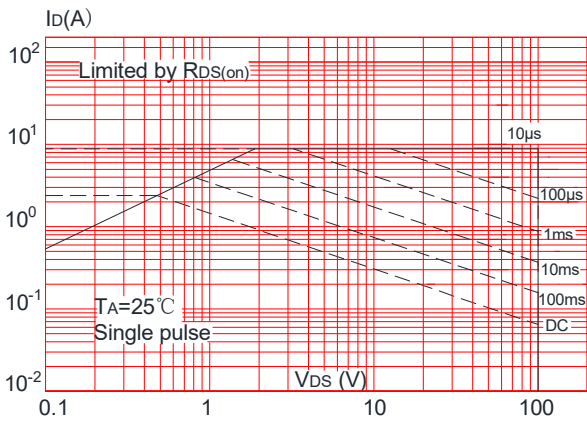


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

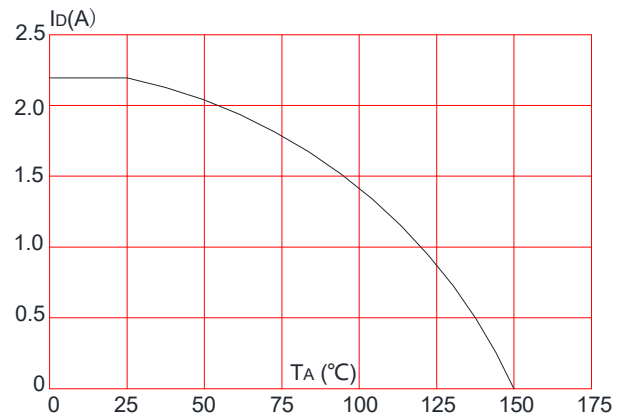
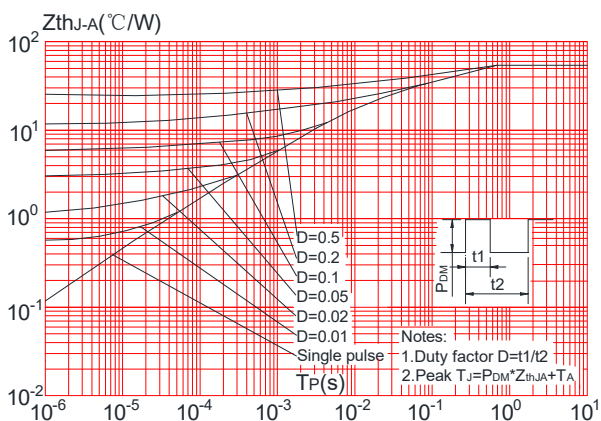


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient





Test Circuit

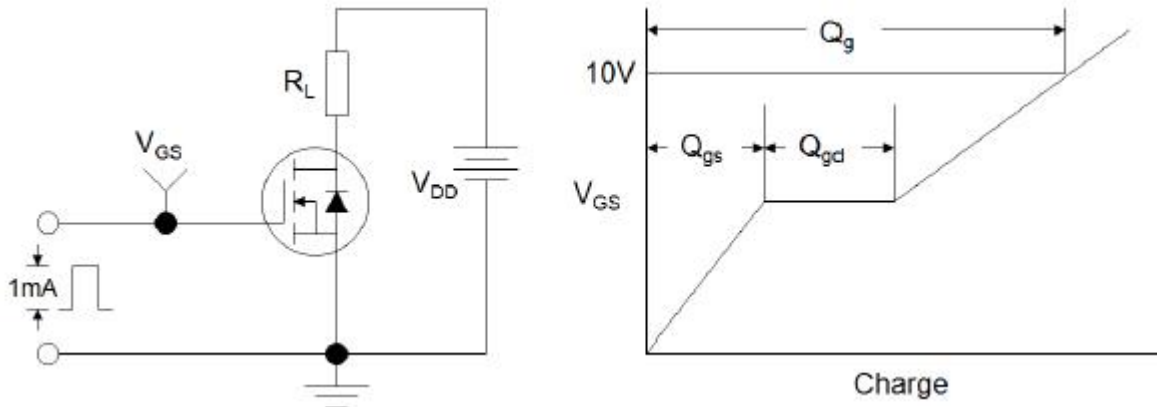


Figure1:Gate Charge Test Circuit & Waveform

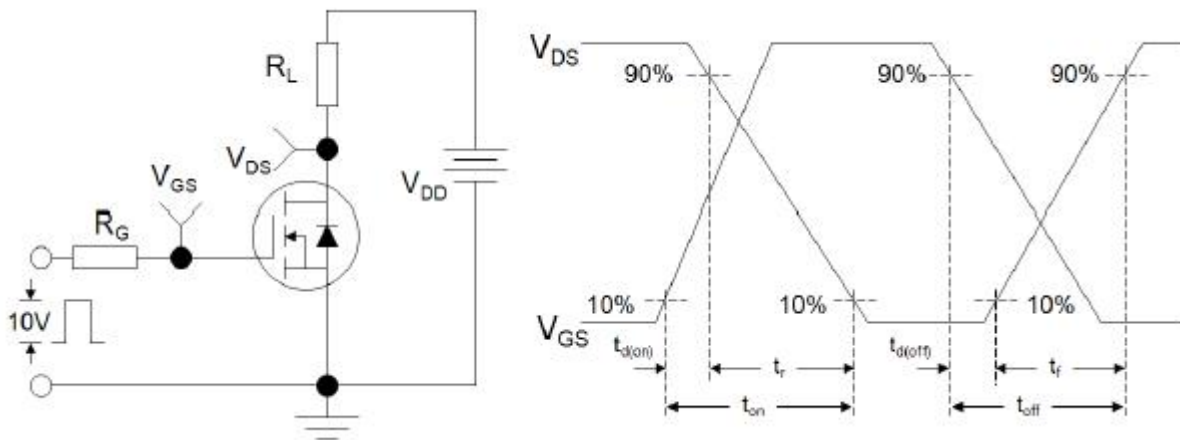


Figure 2: Resistive Switching Test Circuit & Waveforms

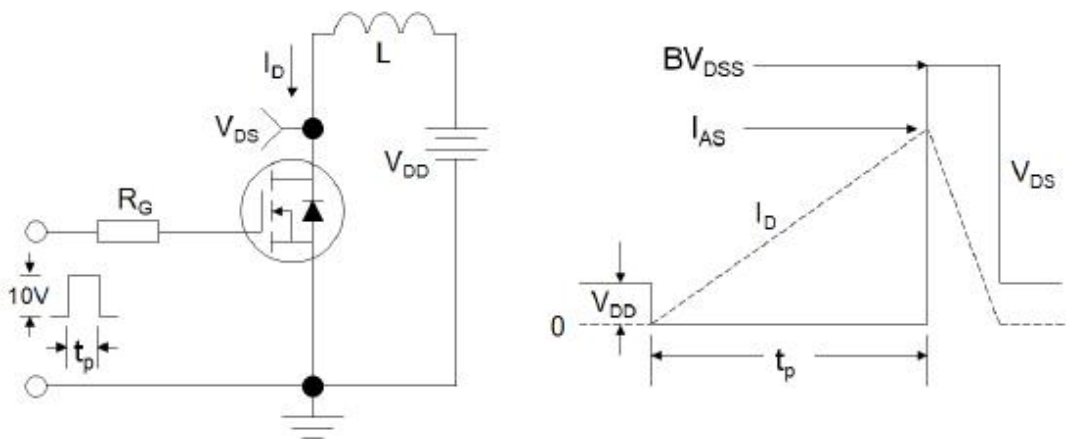
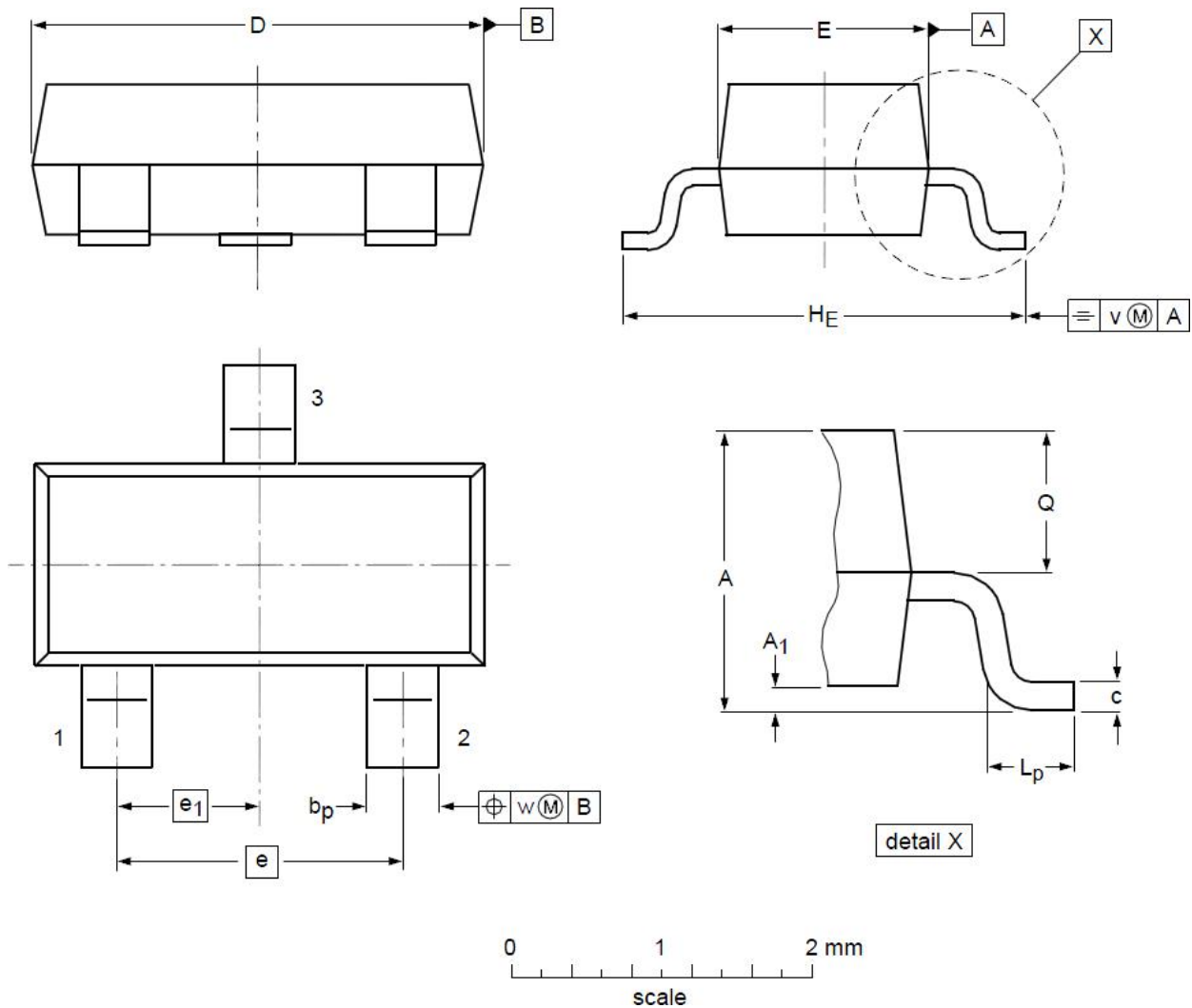


Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms



SOT23 Mechanical Data



DIMENSIONS (unit : mm)

Symbol	Min	Typ	Max	Symbol	Min	Typ	Max
A	0.90	1.01	1.15	A ₁	0.01	0.05	0.10
b _p	0.30	0.42	0.50	c	0.08	0.13	0.15
D	2.80	2.92	3.00	E	1.20	1.33	1.40
e	--	1.90	--	e ₁	--	0.95	--
H _E	2.25	2.40	2.55	L _p	0.30	0.42	0.50
Q	0.45	0.49	0.55	v	--	0.20	--
w	--	0.10	--				